

## GSMBT4403

### PNP EPITAXIAL PLANAR TRANSISTOR

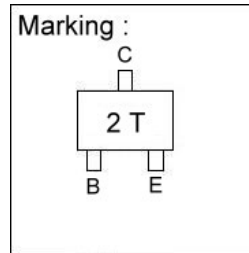
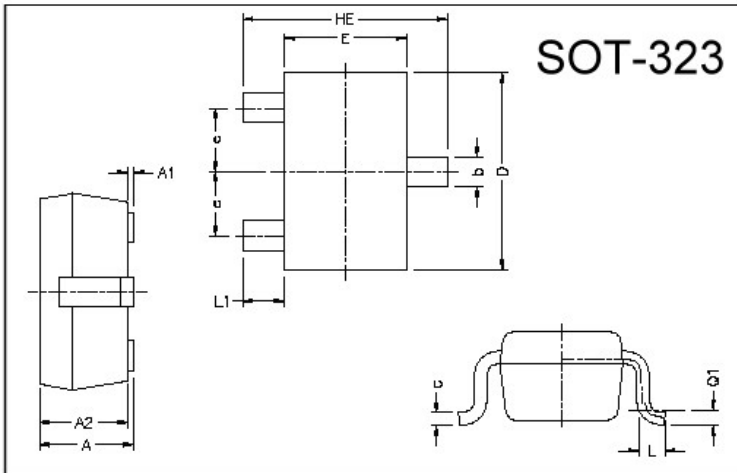
#### Description

The GSMBT4403 is designed for general purpose switching and amplifier applications.

#### Features

- Complementary to GSMBT4401
- High DC Current Gain: 100-300 at 150mA

#### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

#### Absolute Maximum Ratings at Ta = 25°C

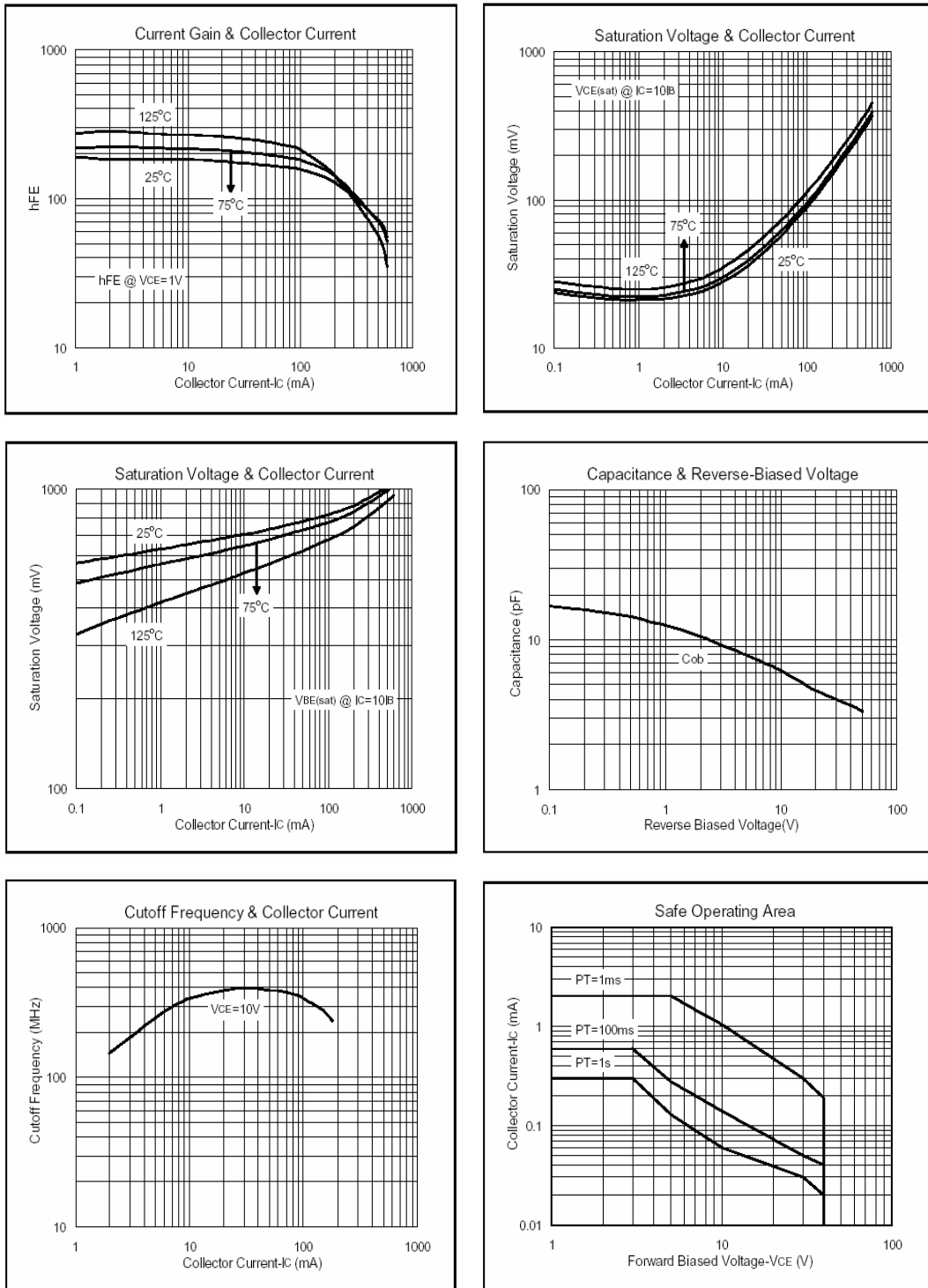
Parameter	Symbol	Ratings	Unit
Junction Temperature	T <sub>j</sub>	+150	°C
Storage Temperature	T <sub>stg</sub>	-55 ~ +150	°C
Collector to Base Voltage at Ta=25°C	VCBO	-40	V
Collector to Emitter Voltage at Ta=25°C	VCEO	-40	V
Emitter to Base Voltage at Ta=25°C	VEBO	-5	V
Collector Current at Ta=25°C	I <sub>C</sub>	-600	mA
Total Power Dissipation at Ta=25°C	PD	225	mW

#### Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-40	-	-	V	I <sub>C</sub> =-100uA
BVCEO	-40	-	-	V	I <sub>C</sub> =-1mA
BVEBO	-5	-	-	V	I <sub>E</sub> =-10uA
ICEX	-	-	-100	nA	V <sub>CE</sub> =-35V, V <sub>BE</sub> =-0.4V
*VCE(sat)1	-	-	-400	mV	I <sub>C</sub> =-150mA, I <sub>B</sub> =-15mA
*VCE(sat)2	-	-	-750	mV	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA
*VBE(sat)1	-	-	-950	mV	I <sub>C</sub> =-150mA, I <sub>B</sub> =-15mA
*VBE(sat)2	-	-	-1.3	V	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA
*hFE1	30	-	-		V <sub>CE</sub> =-1V, I <sub>C</sub> =-0.1mA
*hFE2	60	-	-		V <sub>CE</sub> =-1V, I <sub>C</sub> =-1mA
*hFE3	100	-	-		V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA
*hFE4	100	-	300		V <sub>CE</sub> =-2V, I <sub>C</sub> =-150mA
*hFE5	20	-	-		V <sub>CE</sub> =-2V, I <sub>C</sub> =-500mA
f <sub>T</sub>	200	-	-	MHz	V <sub>CE</sub> =-10V, I <sub>C</sub> =-20mA, f=100MHz
C <sub>ob</sub>	-	-	8.5	pF	V <sub>CE</sub> =-10V, f=1MHz

\* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

## Characteristics Curve



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